

10/019244

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JC13 Rec'd PCT/PTO 21 DEC 2001

FORM PTO-1449 (Modified)		ATTY. DOCKET NO. 1446NP	SERIAL NO. To Be Assigned
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		APPLICANT: Prasad Narhar GADGIL	
(Use several sheets if necessary)		FILING DATE: Herewith	GROUP: To Be Assigned

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
ANL	4 9 9 3 3 5 7	02/19/91	Scholz	118	715	
ANL	5 2 4 2 5 3 0	09/07/93	Batey et al.	156	613	
ANL	5 2 5 6 2 0 5	10/26/93	Schmitt, III et al.	118	723	
ANL	5 2 8 1 2 7 4	01/25/94	Yoder	118	697	
ANL	5 3 1 6 7 9 3	05/31/94	Wallace et al.	427	248-1	
ANL	5 3 4 2 6 6 0	08/30/94	Cann et al.	427	577	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
ANL	0 0 1 5 3 9 0	17.09.80	EPO	—	—	

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

ANL	<input checked="" type="checkbox"/> Hurle, D.T.J., "Thin Films and Epitaxy," Handbook of Crystal Growth, Vol. 3, 1994, pp. 606-663.
ANL	<input checked="" type="checkbox"/> Liu, H. et al., "GaAs Atomic Layer Epitaxy in a Rotating Disc Reactor," SPIE, Vol. 1676, 1992, pp. 20-25.

EXAMINER	DATE CONSIDERED
ANL	11/25/03

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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EXAMINER INITIALS	DOCUMENT NUMBER				DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)			
JNL	5	8	1	0	9	4	2	09/22/98	Narayanswami et al.	134	71	
JNL	5	8	7	9	4	5	9	03/09/99	Gadgil et al.	118	715	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

McIntosh, F.G. et al., "Silicon Monolayer Growth Using Dichlorosilane and Hydrogen in a Near Atmospheric Pressure Chemical Vapor Deposition Reactor," *Thin Solid Films* 225, 1993, pp. 183-186

Reid, K.G. et al., "The Role of Gas Phase Decomposition in the Ale Growth of III-V Compounds," North Carolina State University, Electrical & Computer Engineering Dept., Raleigh, NC., pp. 133-138.

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1125/03

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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

Surmikeris, J. et al., "Layer-by-Layer Epitaxial Growth of GaN at Low Temperatures," *Thin Solid Films*, 1993, pp. 244-249.

Usui, Akira, "Atomic Layer Epitaxy of III-V Compounds: Chemistry and Applications," *Proceedings of the IEEE*, Vol. 80, No. 10, October 1992, pp. 1641-1653.

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ER
Mark H.

DATE CONSIDERED

11/15/03

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